

Pat nt Abstracts f Japan

PUBLICATION NUMBER : 58111318
PUBLICATION DATE : 02-07-83

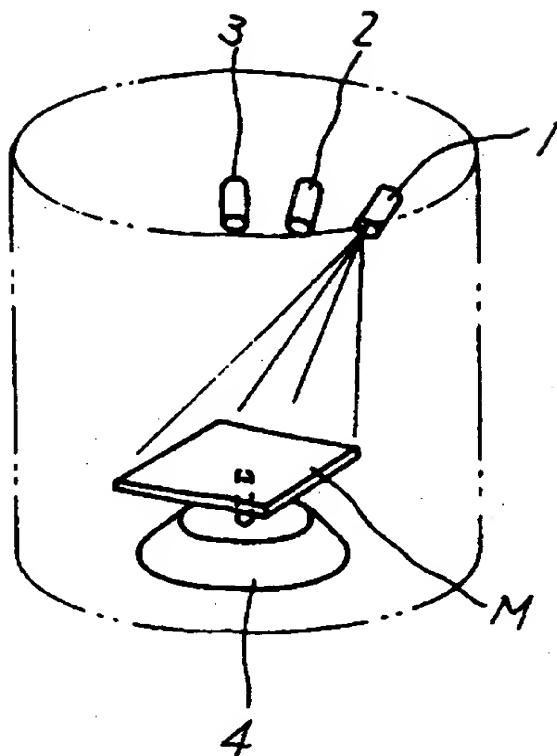
APPLICATION DATE : 25-12-81
APPLICATION NUMBER : 56209252

APPLICANT : HITACHI LTD;

INVENTOR : SATO TETSURO;

INT.CL : H01L 21/30

TITLE : DEVELOPING METHOD



ABSTRACT : **PURPOSE:** To reduce the small-dimension variations among portions in a mask and chips in a wafer, by preparing two or more developers various in concentration, and successively using them in order of concentration, i.e. from the thick to the thin.

CONSTITUTION: A mask M coated with a photoresist as well as subjected to a pattern lithography is secured onto a spinner 4 and is stationary or rotating. A thick developer is applied to the mask M from a nozzle 1 by the spray or shower system. when a time t_1 has elapsed, a thin developer is supplied from a nozzle 2, and further at a time t_2 , a rinsing pure water is supplied from a nozzle 3. Since the developers various in concentration are prepared and used in order of concentration, from the thick to the thin, it is possible to obtain various effects offered by the thin developer conjointly with the high-speed developing effect by the thick developer.

COPYRIGHT: (C) JPO